

Form PTO-1449 US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known Application Number: 10/813,565 Filing Date: March 30, 2004 First Named Inventor: Yuji HORI Art Unit: 2811 Examiner Name: Cuong Quang Nguyen Confirmation No.: 4125	
Sheet	1	of	2	Attorney Docket No.: 800_134	

U.S. PATENT DOCUMENTS

Exam. Initial		Document Number	Date	Name	Our Docket No.	Class	Sub Class	Filing Date
Ch	AA	2002/0053679 A1	05/09/2002	Nikolaev et al.				
Ch	AB	2002/0136932 A1	09/26/2002	Yoshida				
Ch	AC	5,488,233	01/30/1996	Ishikawa et al.				
Ch	AD	5,740,192	04/14/1998	Hatano et al.				

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		Document Number	Date	Country	Class	Sub Class	Translation	Abstract
Ch	AE	1 211 737 A2	06/05/2002	EP				
Ch	AF	00/63961	10/26/2000	WO				

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages etc.)

Ch	AG	SHIBATA T ET AL: "Characterization of high-quality epitaxial AlN films grown by MOVPE", GAN AND RELATED ALLOYS - 2001. Symposium (Materials Research Society Symposium Proceedings Vol. 693), GAN AND RELATED ALLOYS - 2001, BOSTON, MA, USA, 26-30 JAN. 2001, pages 541-544, XP001168620, 2002, Warrendale, PA, USA, Mater. Res. Soc., USA *abstract*
Ch	AH	SAXLER A ET AL: "High quality aluminum nitride epitaxial layers grown on sapphire substrates", APPLIED PHYSICS LETTERS, 17 JAN. 1994, USA, vol. 64, no. 3, pages 339-341, XP002256572, ISSN: 0003-6951 *page 340*
Ch	AI	OHBA Y ET AL: "Growth of high-quality AlN and AlN/GaN/AlN heterostructure on sapphire substrate" JAPANESE JOURNAL OF APPLIED PHYSICS, PART 2 (LETTERS), 15 AUG. 1996, PUBLICATION OFFICE JAPANESE JOURNAL APPL. PHYS. JAPAN, vol. 35, no. 8B, pages L1013-L1015, XP002256573, ISSN: 0021-4922 *L1013-L1014*
Ch	AJ	KAUFMANN U ET AL: "Hole conductivity and compensation in epitaxial GaN:Mg layers" PHYSICAL REVIEW B (CONDENSED MATTER), 15 OCT. 2000, APS THROUGH AIP, USA, vol. 62, no. 16, pages 10867-10872, XP002256574, ISSN: 0163-1829 *page 10867*
Ch	AK	SANTIC B ET AL: "Current transport mechanism and I-V characteristics of titanium and indium contacts to p-type GaN" MATERIALS SCIENCE & ENGINEERING B (SOLID-STATE MATERIALS FOR ADVANCED TECHNOLOGY), 30 MAY 2002, ELSEVIER, SWITZERLAND, vol. B93, pages 202-206, XP002255818, ISSN: 0921-5107, *the whole document*

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Yuji HORI

Art Unit

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Examiner Name

Cuong Quang Nguyen

Confirmation No.

4125

<i>a</i>	AK	BHARGAVA R N: "The role of impurity in doped nanocrystals" 1996 INTERNATIONAL CONFERENCE ON LUMINESCENCE AND OPTICAL SPECTROSCOPY OF CONDENSED MATTER, PRAGUE, CZECH REPUBLIC, 18-23 AUG. 1996, vol. 72-74, pages 46-48, XP002255817, Journal of Luminscence, June 1997, Elsevier, Netherlands, ISSN: 0022-2313 *the whole document*
<i>in</i>	AL	ZHANG J ET AL: "INGAN SELF-ASSEMBLED QUANTUM DOTS GROWN BY METALORGANIC CHEMICAL-VAPOR DEPOSITION WITH INDIUM AS THE ANTISURFACTANT" APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, NEW YORK, US, vol. 80, no. 3, 21 January 2002 (2002-01-21), pages 485-487, XP001093504, ISSN: 0003-6951 *page 485*

Examiner:	<i>ALG</i>	Date Considered:	<i>05-01-05</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*In accordance with the Notice dated July 11, 2003 on the PTO website, we are not enclosing copies of any of the above U.S. references.